

SEMITOP[®] 4

IGBT Module

SK75GD126T

Preliminary Data

Features

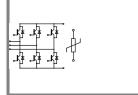
- One screw mounting module
- Fully compatible with SEMITOP[®]1,2,3
- Improved thermal performances
 by aluminium oxide substrate
- Trench IGBT technology
- CAL technology FWD
- Integrated NTC temperature sensor

Typical Applications*

- Inverter up to 42 kVA
- Typ. motor power 18,5 kW

Absolute Maximum Ratings			$T_s = 2$	= 25 °C, unless otherwise specified			
Symbol	-			Values			
IGBT							
V _{CES}	T _j = 25 °C			1200	V		
I _C	T _j = 150 °C	T _s = 25 °C		88	А		
		T _s = 70 °C		67	А		
I _{CRM}	I _{CRM} = 2 x I _{Cnom}			140	А		
V _{GES}				± 20	V		
t _{psc}	V_{CC} = 600 V; $V_{GE} \le 20$ V; VCES < 1200 V	T _j = 125 °C		10	μs		
Inverse	Diode						
I _F	T _j = 150 °C	T _s = 25 °C		91	Α		
		T _s = 70 °C		68	А		
I _{FRM}	I _{FRM} = 2 x I _{Fnom}			150	А		
Module							
I _{t(RMS)}					А		
T _{vj}				-40 +150	°C		
T _{stg}				-40 +125	°C		
V _{isol}	AC, 1 min.			2500	V		

Characteristics T _s =			25 °C, unless otherwise specified				
Symbol	Conditions		min.	typ.	max.	Units	
IGBT							
V _{GE(th)}	V_{GE} = V_{CE} , I_C = 3 mA		5	5,8	6,5	V	
I _{CES}	V_{GE} = 0 V, V_{CE} = V_{CES}	T _j = 25 °C			0,0094	mA	
		T _j = 125 °C				mA	
I _{GES}	V _{CE} = 0 V, V _{GE} = 20 V	T _j = 25 °C			1200	nA	
		T _j = 125 °C				nA	
V _{CE0}		T _j = 25 °C		1	1,2	V	
		T _j = 125 °C		0,9	1,1	V	
r _{CE}	V _{GE} = 15 V	T _j = 25°C		10	13	mΩ	
		T _j = 125°C		16	19	mΩ	
V _{CE(sat)}	I _{Cnom} = 75 A, V _{GE} = 15 V			1,7	2,1	V	
		T _j = 125°C _{chiplev.}		2	2,4	V	
C _{ies}				5		nF	
C _{oes}	V_{CE} = 25, V_{GE} = 0 V	f = 1 MHz		0,26		nF	
C _{res}				0,23		nF	
t _{d(on)}				62		ns	
t,	R _{Gon} = 8,2 Ω	V _{CC} = 600V		32		ns	
E _{on}	di/dt = 1340 A/µs	I _C = 75A		11,3		mJ	
t _{d(off)}	R_{Goff} = 8,2 Ω	T _j = 125 °C		514		ns	
t _f	di/dt = 1340 A/µs	V _{GE} = -7/+15 V		90		ns	
E _{off}				10		mJ	
R _{th(j-s)}	per IGBT			0,5		K/W	



GD-T



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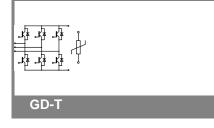
Typical Applications*

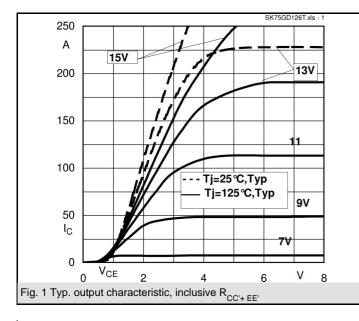
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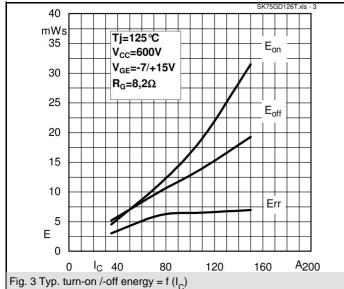
Symbol	Conditions		min.	typ.	max.	Units
Inverse D						
$V_F = V_{EC}$	I _{Fnom} = 75 A; V _{GE} = 0 V	T _j = 25 °C _{chiplev.}		1,46		V
		T _j = 125 °C _{chiplev.}		1,4		V
V _{F0}		T _j = 25 °C		1,05		V
		T _j = 125 °C		0,95		V
r _F		T _j = 25 °C		5,5		mΩ
		T _j = 125 °C		6		mΩ
I _{RRM}	I _F = 75 A	T _j = 125 °C		70		Α
Q _{rr}	di/dt = 1340 A/µs			20		μC
E _{rr}	V _{CC} = 600V			6		mJ
R _{th(j-s)D}	per diode			0,7		K/W
M _s	to heat sink		2,5		2,75	Nm
w				60		g
Temperat	ture sensor					
R ₁₀₀	T _s =100°C (R ₂₅ =5kΩ)			493±5%		Ω

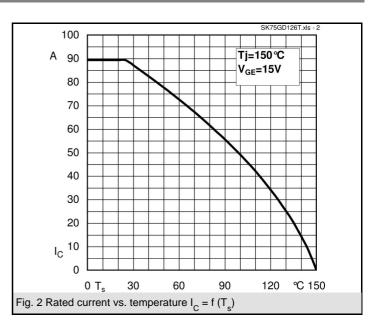
This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, Chapter IX.

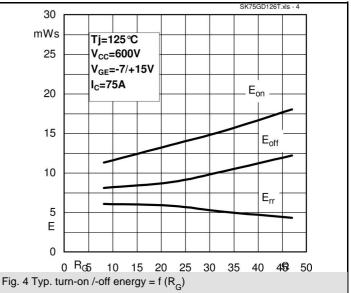
* The specifications of our components may not be considered as an assurance of component characteristics. Components have to be tested for the respective application. Adjustments may be necessary. The use of SEMIKRON products in life support appliances and systems is subject to prior specification and written approval by SEMIKRON. We therefore strongly recommend prior consultation of our personal.

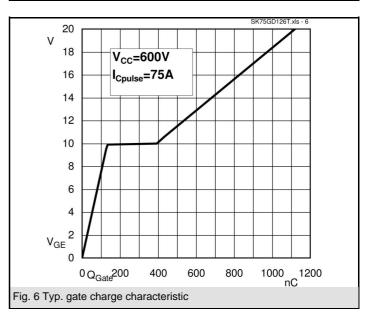


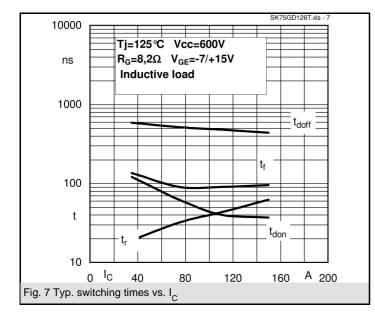


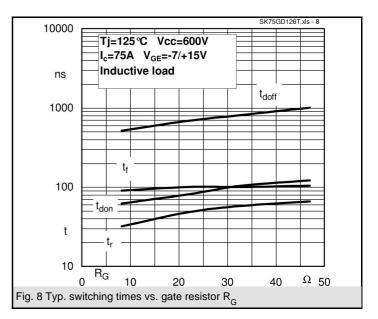


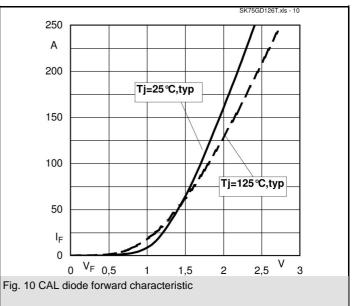












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